

# HD74HCT1G04

# Inverter

REJ03D0193-0500Z (Previous ADE-205-303C (Z)) Rev.5.00 Jan.28.2004

#### **Description**

The HD74HCT1G04 is high-speed CMOS inverter using silicon gate CMOS process. With CMOS low power dissipation, it provides high-speed equivalent to LS-TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

#### **Features**

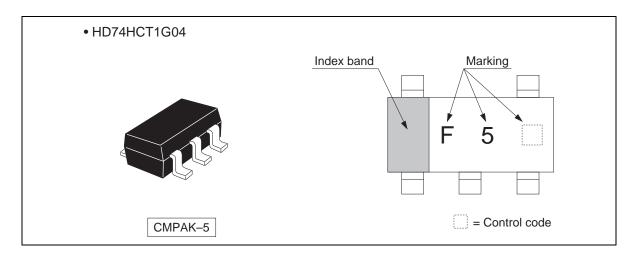
- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- TTL compatible input level. Supply voltage range: 4.5 to 5.5 V

Operating temperature range: -40 to +85°C

- $|I_{OH}| = I_{OL} = 2 \text{ mA (min)}$
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74HCT1G04CME	CMPAK-5 pin	CMPAK-5V	CM	E (3,000 pcs/reel)

#### **Outline and Article Indication**

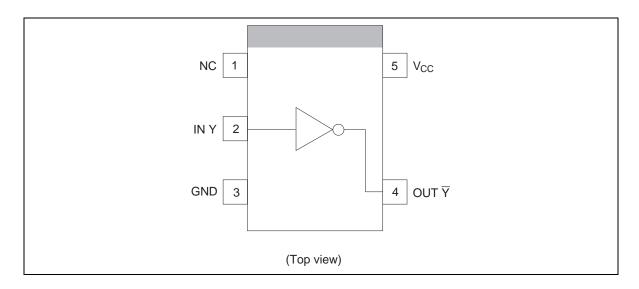


## **Function Table**

Input A	Output Y
Н	L
L	Н

H : High level L : Low level

# **Pin Arrangement**



#### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V	
Input voltage range *1	Vı	$-0.5$ to $V_{CC}$ + 0.5	V	
Output voltage range *1, 2	Vo	$-0.5$ to $V_{CC}$ + 0.5	V	Output : H or L
Input clamp current	I <sub>IK</sub>	±20	mA	$V_I < 0$ or $V_I > V_{CC}$
Output clamp current	I <sub>OK</sub>	±20	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I <sub>O</sub>	±25	mA	$V_O = 0$ to $V_{CC}$
Continuous current through V <sub>CC</sub> or GND	I <sub>CC</sub> or I <sub>GND</sub>	±25	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P <sub>T</sub>	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

# **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Test Conditions
Supply voltage range	Vcc	4.5	5.5	V	
Input voltage range	Vı	0	5.5	V	
Output voltage range	Vo	0	V <sub>CC</sub>	V	
Output current	I <sub>OL</sub>	_	2	mA	V <sub>CC</sub> = 4.5 to 5.5 V
	I <sub>OH</sub>	_	-2		$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
Input rise / fall time (0.3 V to 2.7 V)	t <sub>r</sub> , t <sub>f</sub>	0	500	ns	V <sub>CC</sub> = 4.5 to 5.5 V
Operating temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

## HD74HCT1G04

# **Electrical Characteristics**

		$\mathbf{V}_{\text{CC}}$	T <sub>a</sub> = 2	5°C		$T_a = -4$	$T_a = -40 \text{ to } 85^{\circ}\text{C}$			
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Con	ditions
Input voltage	$V_{IH}$	4.5 to 5.5	2.0	_	_	2.0	_	V		
	V <sub>IL</sub>	4.5 to 5.5	_	_	8.0	_	0.8	-		
Output voltage	V <sub>OH</sub>	4.5	4.4	4.5	_	4.4	_	V	$V_{\text{IN}} = V_{\text{IL}}$	$I_{OH} = -20 \mu A$
		4.5	4.18	4.31	_	4.13	_	=		$I_{OH} = -2 \text{ mA}$
	V <sub>OL</sub>	4.5		0.0	0.1	_	0.1	_	$V_{IN} = V_{IH}$	I <sub>OL</sub> = 20 μA
		4.5	_	0.17	0.26	_	0.33	=		I <sub>OL</sub> = 2 mA
Input current	I <sub>IN</sub>	5.5	_	_	±0.1	_	±1.0	μΑ	$V_{\text{IN}} = V_{\text{CC}}$	or GND
Operating current	I <sub>CC</sub>	5.5		_	1.0	_	10.0	μΑ	$V_{IN} = V_{CC}$	or GND
Quiescent supply current	I <sub>CCT</sub>	5.5	_	_	2.0	_	2.9	mA	One input $V_{IN} = 2.4 \text{ V}$ , other input $V_{CC}$ or GND	

#### **Switching Characteristics**

 $Ta = 25^{\circ}C$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Output rise / fall time	t <sub>TLH</sub> t <sub>THL</sub>	_	6	10	ns	Test circuit
Propagation delay time	t <sub>PLH</sub>		7.5	12	ns	Test circuit
	t <sub>PHL</sub>	_	10	17		

 $(C_L = 15 \text{ pF}, t_r = t_f = 6 \text{ ns}, V_{CC} = 5 \text{ V})$ 

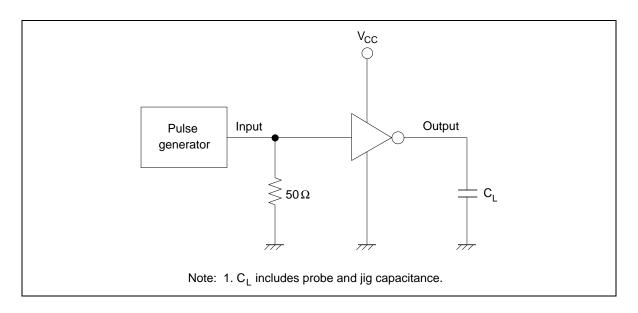
		$\mathbf{v}_{cc}$	Ta =	25°C		Ta = -4	40 to 85°C		
Item	Symbol	(V)	Min	Тур	Max	Min	Max	Unit	Test Conditions
Output rise / fall time	t <sub>TLH</sub> t <sub>THL</sub>	4.5	_	14	25	_	31	ns	Test circuit
Propagation delay time	t <sub>PLH</sub>	4.5	_	11.2	16	_	20	ns	Test circuit
	t <sub>PHL</sub>	4.5	_	16.4	27	_	31	_	
Input capacitance	C <sub>IN</sub>	_	_	2.5	5	_	5	pF	
Equivalent capacitance	C <sub>PD</sub>	_	_	10	_	_	_	pF	

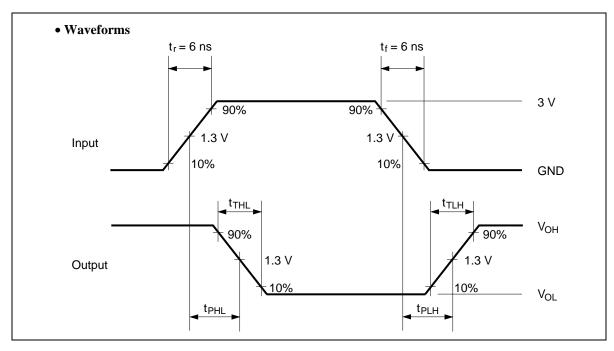
 $<sup>(</sup>C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns})$ 

Note: C<sub>PD</sub> is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression below.

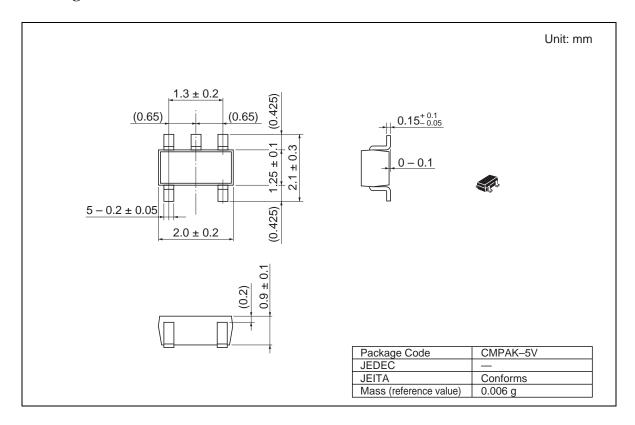
 $I_{CC}$  (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

#### **Test Circuit**





# **Package Dimensions**



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